



# PSMN9R5-100XS

N-channel 100V 9.6 mΩ standard level MOSFET in TO220F (SOT186A)

Rev. 3 — 6 March 2012

Product data sheet

## 1. Product profile

### 1.1 General description

Standard level N-channel MOSFET in TO220F (SOT186A) package qualified to 175°C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Isolated package
- Suitable for standard level gate drive

### 1.3 Applications

- AC-to-DC power supply equipment
- Server power supplies
- Motor control
- Synchronous rectification

### 1.4 Quick reference data

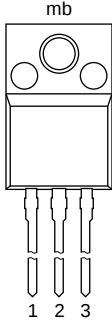
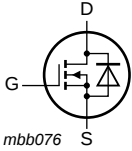
Table 1. Quick reference data

| Symbol                         | Parameter                                    | Conditions                                                                                                                                                                     | Min | Typ  | Max  | Unit |
|--------------------------------|----------------------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|------|------|------|
| $V_{DS}$                       | drain-source voltage                         | $T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$                                                                                                                             | -   | -    | 100  | V    |
| $I_D$                          | drain current                                | $T_{mb} = 25\text{ °C}$ ; $V_{GS} = 10\text{ V}$ ; see <a href="#">Figure 1</a>                                                                                                | -   | -    | 44.2 | A    |
| $P_{tot}$                      | total power dissipation                      | $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>                                                                                                                         | -   | -    | 52.6 | W    |
| <b>Static characteristics</b>  |                                              |                                                                                                                                                                                |     |      |      |      |
| $R_{DS(on)}$                   | drain-source on-state resistance             | $V_{GS} = 10\text{ V}$ ; $I_D = 10\text{ A}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 12</a> ; see <a href="#">Figure 13</a>                                            | -   | 8.15 | 9.6  | mΩ   |
| <b>Dynamic characteristics</b> |                                              |                                                                                                                                                                                |     |      |      |      |
| $Q_{GD}$                       | gate-drain charge                            | $V_{GS} = 10\text{ V}$ ; $I_D = 10\text{ A}$ ; $V_{DS} = 50\text{ V}$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>                                          | -   | 24.3 | -    | nC   |
| $Q_{G(tot)}$                   | total gate charge                            |                                                                                                                                                                                | -   | 81.5 | -    | nC   |
| <b>Avalanche ruggedness</b>    |                                              |                                                                                                                                                                                |     |      |      |      |
| $E_{DS(AL)S}$                  | non-repetitive drain-source avalanche energy | $V_{GS} = 10\text{ V}$ ; $T_{j(init)} = 25\text{ °C}$ ; $I_D = 44.2\text{ A}$ ; $V_{sup} \leq 100\text{ V}$ ; unclamped; $R_{GS} = 50\text{ Ω}$ ; see <a href="#">Figure 3</a> | -   | -    | 260  | mJ   |



2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description             | Simplified outline                                                                | Graphic symbol                                                                      |
|-----|--------|-------------------------|-----------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
| 1   | G      | gate                    |  |  |
| 2   | D      | drain                   |                                                                                   |                                                                                     |
| 3   | S      | source                  |                                                                                   |                                                                                     |
| mb  |        | mounting base; isolated |                                                                                   |                                                                                     |

SOT186A (TO-220F)

3. Ordering information

Table 3. Ordering information

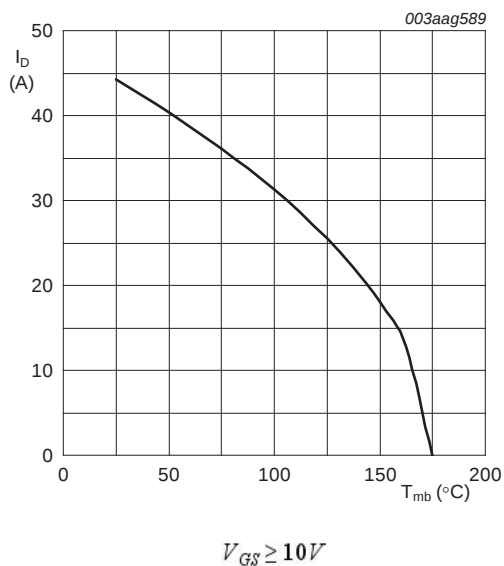
| Type number   | Package |                                                                                                     |         |
|---------------|---------|-----------------------------------------------------------------------------------------------------|---------|
|               | Name    | Description                                                                                         | Version |
| PSMN9R5-100XS | TO-220F | plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack" | SOT186A |

## 4. Limiting values

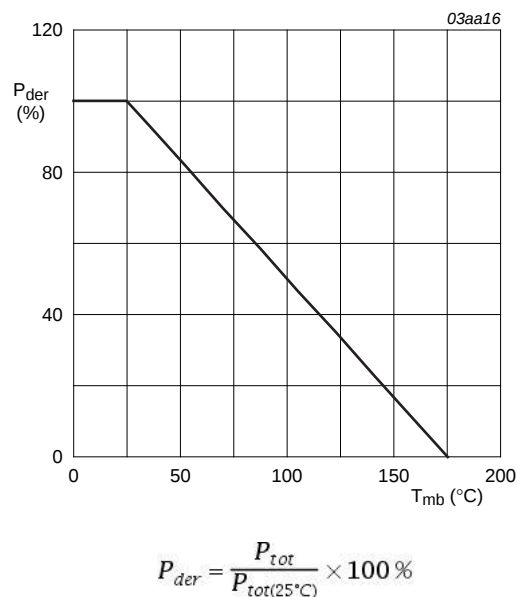
**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol                      | Parameter                                    | Conditions                                                                                                                                                                                 | Min | Max  | Unit |
|-----------------------------|----------------------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|------|------|
| $V_{DS}$                    | drain-source voltage                         | $T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$                                                                                                                                         | -   | 100  | V    |
| $V_{DGR}$                   | drain-gate voltage                           | $T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$ ; $R_{GS} = 20\text{ k}\Omega$                                                                                                          | -   | 100  | V    |
| $V_{GS}$                    | gate-source voltage                          |                                                                                                                                                                                            | -20 | 20   | V    |
| $I_D$                       | drain current                                | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 1</a>                                                                                                            | -   | 44.2 | A    |
|                             |                                              | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 100\text{ °C}$ ; see <a href="#">Figure 1</a>                                                                                                           | -   | 31.3 | A    |
| $I_{DM}$                    | peak drain current                           | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 4</a>                                                                                          | -   | 177  | A    |
| $P_{tot}$                   | total power dissipation                      | $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>                                                                                                                                     | -   | 52.6 | W    |
| $T_{stg}$                   | storage temperature                          |                                                                                                                                                                                            | -55 | 175  | °C   |
| $T_j$                       | junction temperature                         |                                                                                                                                                                                            | -55 | 175  | °C   |
| $T_{slid(M)}$               | peak soldering temperature                   |                                                                                                                                                                                            | -   | 260  | °C   |
| <b>Source-drain diode</b>   |                                              |                                                                                                                                                                                            |     |      |      |
| $I_S$                       | source current                               | $T_{mb} = 25\text{ °C}$                                                                                                                                                                    | -   | 43.8 | A    |
| $I_{SM}$                    | peak source current                          | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$                                                                                                                         | -   | 177  | A    |
| <b>Avalanche ruggedness</b> |                                              |                                                                                                                                                                                            |     |      |      |
| $E_{DS(AL)S}$               | non-repetitive drain-source avalanche energy | $V_{GS} = 10\text{ V}$ ; $T_{j(\text{init})} = 25\text{ °C}$ ; $I_D = 44.2\text{ A}$ ; $V_{sup} \leq 100\text{ V}$ ; unclamped; $R_{GS} = 50\text{ }\Omega$ ; see <a href="#">Figure 3</a> | -   | 260  | mJ   |



**Fig 1. Continuous drain current as a function of mounting base temperature**



**Fig 2. Normalized total power dissipation as a function of mounting base temperature**

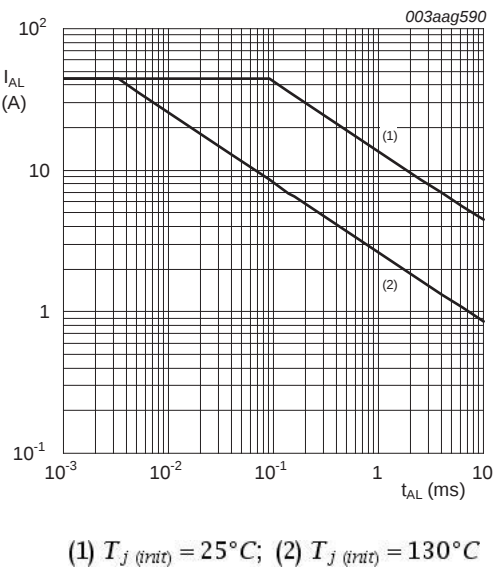


Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time

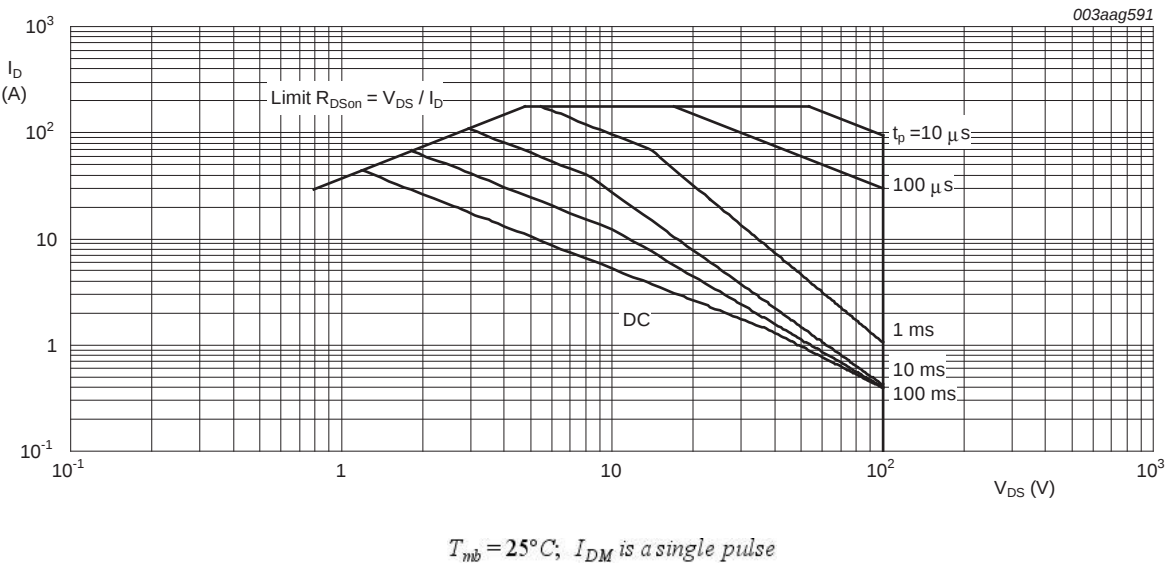
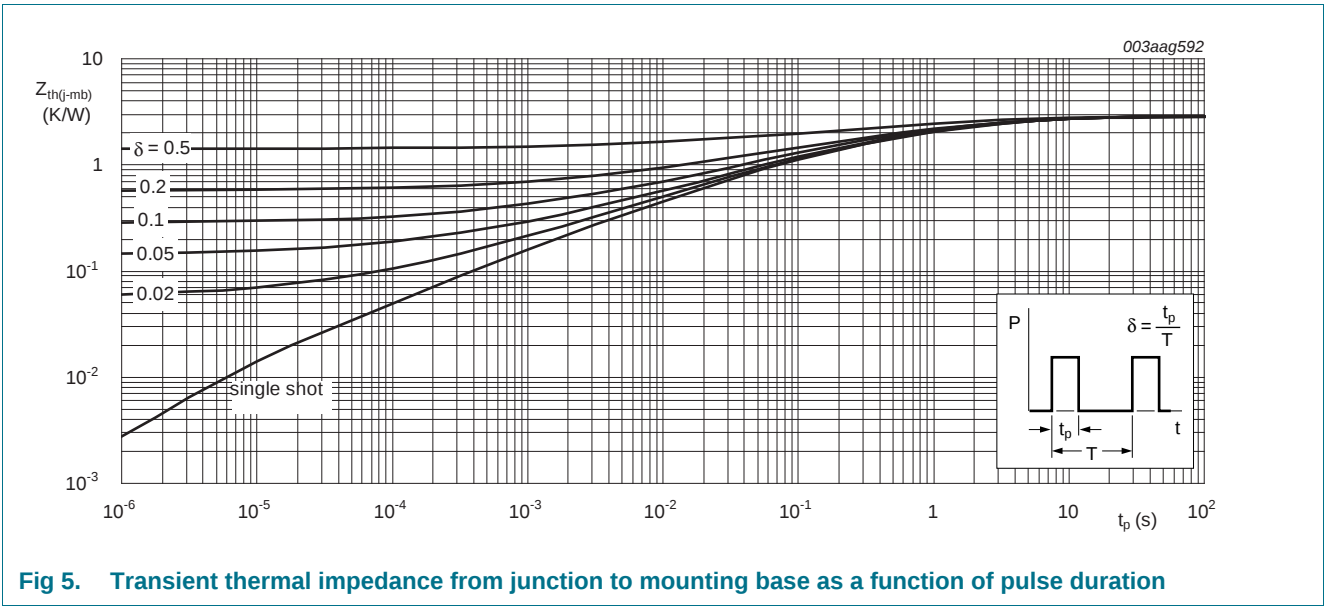


Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol         | Parameter                                         | Conditions                   | Min | Typ | Max  | Unit |
|----------------|---------------------------------------------------|------------------------------|-----|-----|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | see <a href="#">Figure 5</a> | -   | 2.6 | 2.85 | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient       | vertical in free air         | -   | 55  | -    | K/W  |



6. Isolation characteristics

Table 6. Isolation characteristics

| Symbol          | Parameter             | Conditions                                                             | Min                   | Typ | Max  | Unit |
|-----------------|-----------------------|------------------------------------------------------------------------|-----------------------|-----|------|------|
| $C_{isol}$      | isolation capacitance |                                                                        | <a href="#">[1]</a> - | 10  | -    | pF   |
| $V_{isol(RMS)}$ | RMS isolation voltage | 50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; sinusoidal waveform; clean and dust free | -                     | -   | 2500 | V    |

[1] f = 1 MHz

## 7. Characteristics

Table 7. Characteristics

| Symbol                         | Parameter                         | Conditions                                                                                                                                                        | Min | Typ   | Max  | Unit          |
|--------------------------------|-----------------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|-------|------|---------------|
| <b>Static characteristics</b>  |                                   |                                                                                                                                                                   |     |       |      |               |
| $V_{(BR)DSS}$                  | drain-source breakdown voltage    | $I_D = 250\ \mu\text{A}; V_{GS} = 0\ \text{V}; T_J = 25\ ^\circ\text{C}$                                                                                          | 100 | -     | -    | V             |
|                                |                                   | $I_D = 250\ \mu\text{A}; V_{GS} = 0\ \text{V}; T_J = -55\ ^\circ\text{C}$                                                                                         | 90  | -     | -    | V             |
| $V_{GS(th)}$                   | gate-source threshold voltage     | $I_D = 1\ \text{mA}; V_{DS} = V_{GS}; T_J = 25\ ^\circ\text{C};$<br>see <a href="#">Figure 10</a> ; see <a href="#">Figure 11</a>                                 | 2   | 3     | 4    | V             |
|                                |                                   | $I_D = 1\ \text{mA}; V_{DS} = V_{GS}; T_J = 175\ ^\circ\text{C};$<br>see <a href="#">Figure 10</a>                                                                | 1   | -     | -    | V             |
|                                |                                   | $I_D = 1\ \text{mA}; V_{DS} = V_{GS}; T_J = -55\ ^\circ\text{C};$<br>see <a href="#">Figure 10</a>                                                                | -   | -     | 4.6  | V             |
| $I_{DSS}$                      | drain leakage current             | $V_{DS} = 100\ \text{V}; V_{GS} = 0\ \text{V}; T_J = 25\ ^\circ\text{C}$                                                                                          | -   | -     | 4    | $\mu\text{A}$ |
|                                |                                   | $V_{DS} = 100\ \text{V}; V_{GS} = 0\ \text{V}; T_J = 100\ ^\circ\text{C}$                                                                                         | -   | -     | 80   | $\mu\text{A}$ |
| $I_{GSS}$                      | gate leakage current              | $V_{GS} = 20\ \text{V}; V_{DS} = 0\ \text{V}; T_J = 25\ ^\circ\text{C}$                                                                                           | -   | 2     | 100  | nA            |
|                                |                                   | $V_{GS} = -20\ \text{V}; V_{DS} = 0\ \text{V}; T_J = 25\ ^\circ\text{C}$                                                                                          | -   | 2     | 100  | nA            |
| $R_{DS(on)}$                   | drain-source on-state resistance  | $V_{GS} = 10\ \text{V}; I_D = 10\ \text{A}; T_J = 25\ ^\circ\text{C};$<br>see <a href="#">Figure 12</a> ; see <a href="#">Figure 13</a>                           | -   | 8.15  | 9.6  | mΩ            |
|                                |                                   | $V_{GS} = 10\ \text{V}; I_D = 10\ \text{A}; T_J = 100\ ^\circ\text{C};$<br>see <a href="#">Figure 13</a>                                                          | -   | 14.25 | 16.8 | mΩ            |
|                                |                                   | $V_{GS} = 10\ \text{V}; I_D = 10\ \text{A}; T_J = 175\ ^\circ\text{C};$<br>see <a href="#">Figure 13</a>                                                          | -   | 22.8  | 26.9 | mΩ            |
| $R_G$                          | internal gate resistance (AC)     | $f = 1\ \text{MHz}$                                                                                                                                               | -   | 0.7   | -    | Ω             |
| <b>Dynamic characteristics</b> |                                   |                                                                                                                                                                   |     |       |      |               |
| $Q_{G(tot)}$                   | total gate charge                 | $I_D = 10\ \text{A}; V_{DS} = 50\ \text{V}; V_{GS} = 10\ \text{V};$<br>see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>                              | -   | 81.5  | -    | nC            |
| $Q_{GS}$                       | gate-source charge                |                                                                                                                                                                   | -   | 15.6  | -    | nC            |
| $Q_{GS(th)}$                   | pre-threshold gate-source charge  |                                                                                                                                                                   | -   | 11.9  | -    | nC            |
| $Q_{GS(th-pl)}$                | post-threshold gate-source charge |                                                                                                                                                                   | -   | 3.7   | -    | nC            |
| $Q_{GD}$                       | gate-drain charge                 |                                                                                                                                                                   | -   | 24.3  | -    | nC            |
| $V_{GS(pl)}$                   | gate-source plateau voltage       | $I_D = 10\ \text{A}; V_{DS} = 50\ \text{V};$<br>see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>                                                     | -   | 4     | -    | V             |
| $C_{iss}$                      | input capacitance                 | $V_{DS} = 50\ \text{V}; V_{GS} = 0\ \text{V}; f = 1\ \text{MHz};$<br>$T_J = 25\ ^\circ\text{C};$ see <a href="#">Figure 16</a> ;<br>see <a href="#">Figure 17</a> | -   | 4454  | -    | pF            |
| $C_{oss}$                      | output capacitance                | $V_{DS} = 50\ \text{V}; V_{GS} = 0\ \text{V}; f = 1\ \text{MHz};$<br>$T_J = 25\ ^\circ\text{C};$ see <a href="#">Figure 16</a>                                    | -   | 302   | -    | pF            |
| $C_{rss}$                      | reverse transfer capacitance      | $V_{DS} = 50\ \text{V}; V_{GS} = 0\ \text{V}; f = 1\ \text{MHz};$<br>$T_J = 25\ ^\circ\text{C};$ see <a href="#">Figure 16</a> ;<br>see <a href="#">Figure 17</a> | -   | 185   | -    | pF            |
| $t_{d(on)}$                    | turn-on delay time                | $V_{DS} = 50\ \text{V}; R_L = 5\ \Omega; V_{GS} = 10\ \text{V};$<br>$R_{G(ext)} = 4.7\ \Omega; T_J = 25\ ^\circ\text{C}$                                          | -   | 21    | -    | ns            |
| $t_r$                          | rise time                         |                                                                                                                                                                   | -   | 22    | -    | ns            |
| $t_{d(off)}$                   | turn-off delay time               |                                                                                                                                                                   | -   | 68    | -    | ns            |
| $t_f$                          | fall time                         |                                                                                                                                                                   | -   | 33    | -    | ns            |

Table 7. Characteristics ...continued

| Symbol             | Parameter             | Conditions                                                                         | Min | Typ  | Max | Unit |
|--------------------|-----------------------|------------------------------------------------------------------------------------|-----|------|-----|------|
| Source-drain diode |                       |                                                                                    |     |      |     |      |
| $V_{SD}$           | source-drain voltage  | $I_S = 10\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_J = 25\text{ °C}$ ; see Figure 18 | -   | 0.76 | 1.2 | V    |
| $t_{rr}$           | reverse recovery time | $I_S = 10\text{ A}$ ; $di_S/dt = -100\text{ A}/\mu\text{s}$ ;                      | -   | 61.5 | -   | ns   |
| $Q_r$              | recovered charge      | $V_{GS} = 0\text{ V}$ ; $V_{DS} = 50\text{ V}$                                     | -   | 157  | -   | nC   |

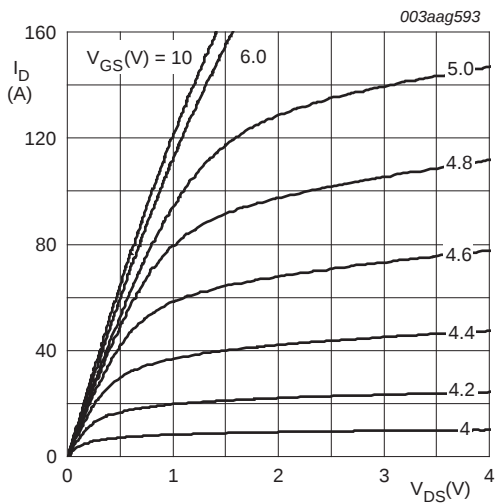


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values

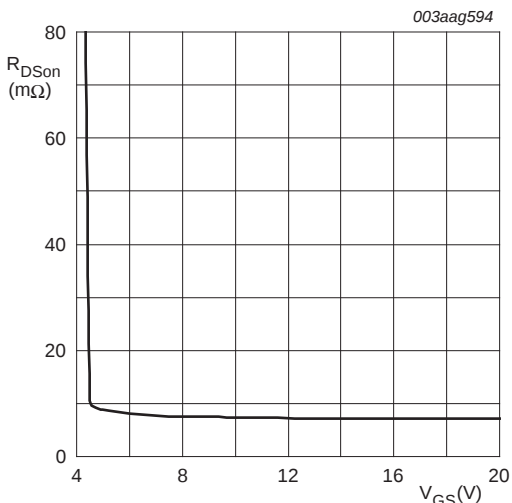


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

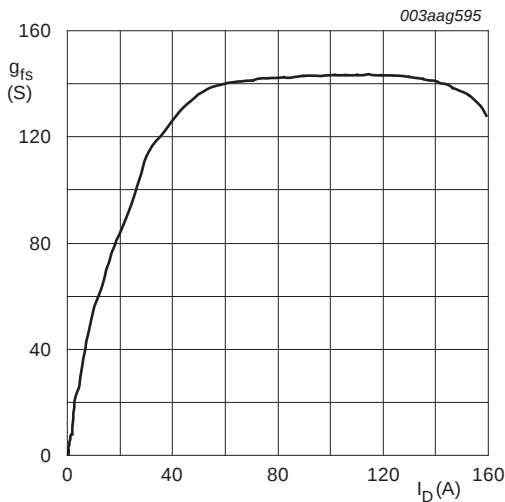


Fig 8. Forward transconductance as a function of drain current; typical values

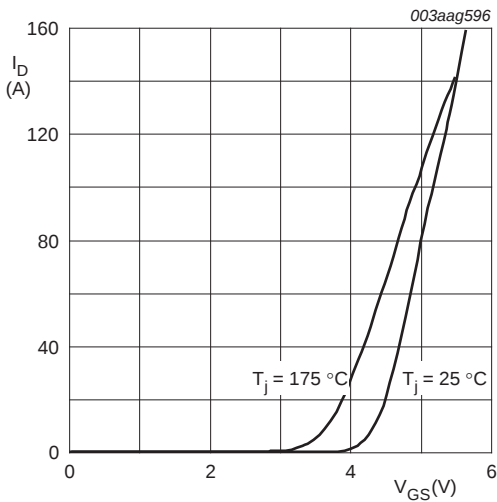
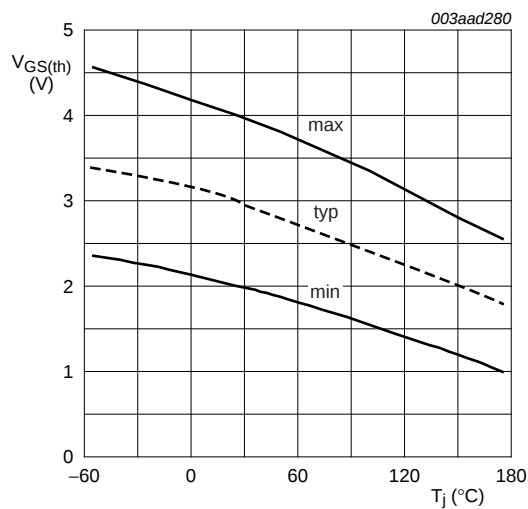
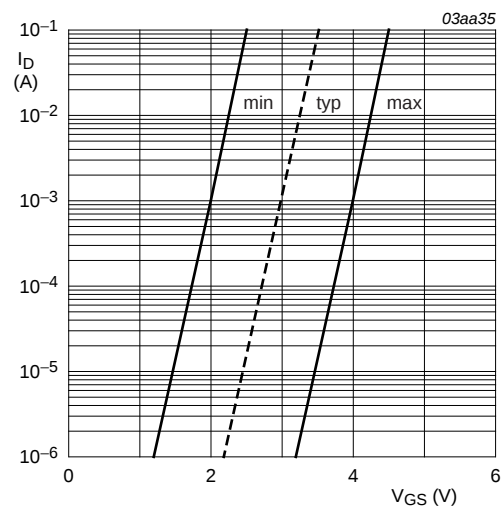


Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values



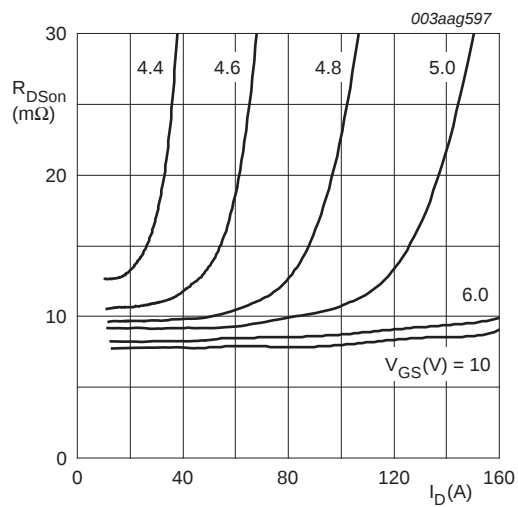
$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature



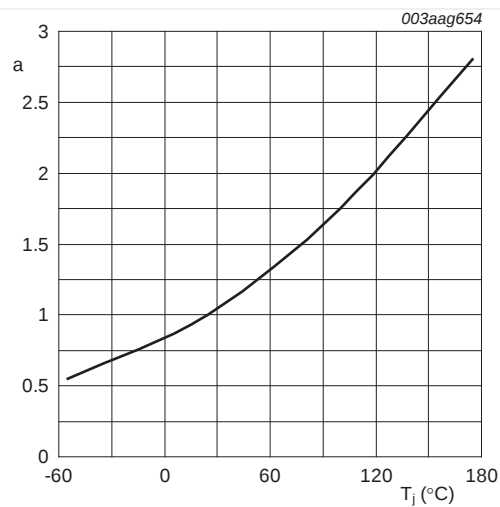
$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$

Fig 11. Sub-threshold drain current as a function of gate-source voltage



$T_j = 25^\circ\text{C}$

Fig 12. Drain-source on-state resistance as a function of drain current; typical values



$a = \frac{R_{DSon}}{R_{DSon}(25^\circ\text{C})}$

Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

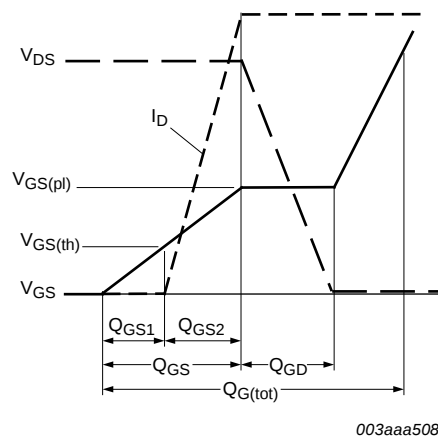
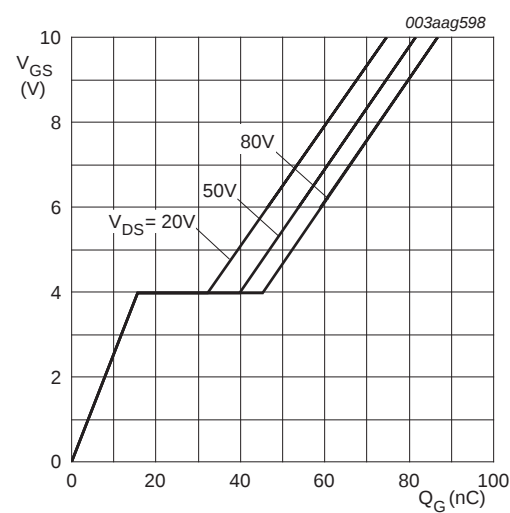
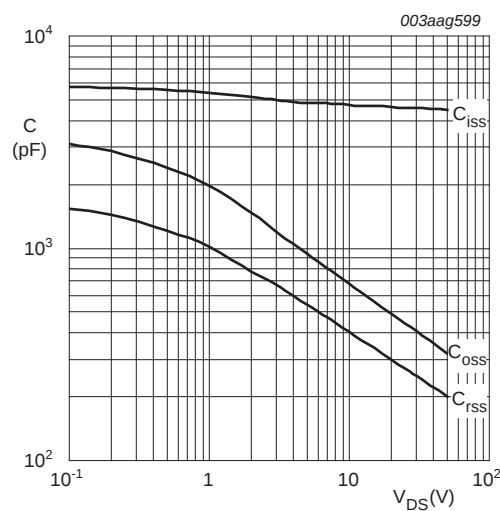


Fig 14. Gate charge waveform definitions



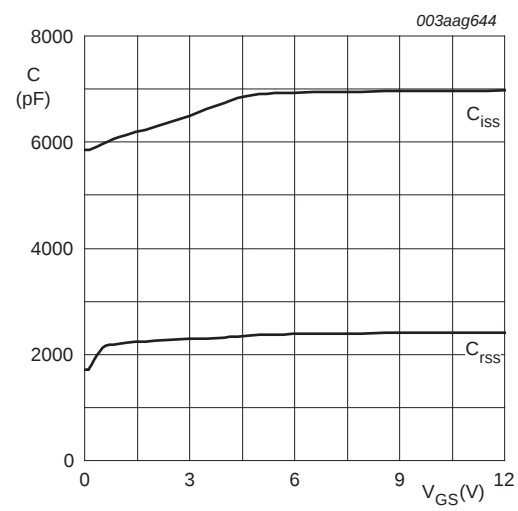
$T_j = 25^{\circ}C$ ;  $I_D = 10A$

Fig 15. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0V$ ;  $f = 1MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$f = 1MHz$ ;  $V_{DS} = 0V$

Fig 17. Input and reverse transfer capacitances as a function of gate-source voltage, typical values

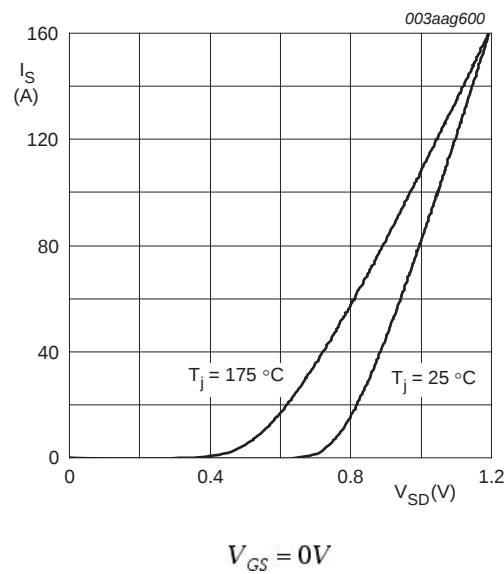


Fig 18. Source current as a function of source-drain voltage; typical values

8. Package outline

Plastic single-ended package; isolated heatsink mounted;  
1 mounting hole; 3-lead TO-220 'full pack'

SOT186A

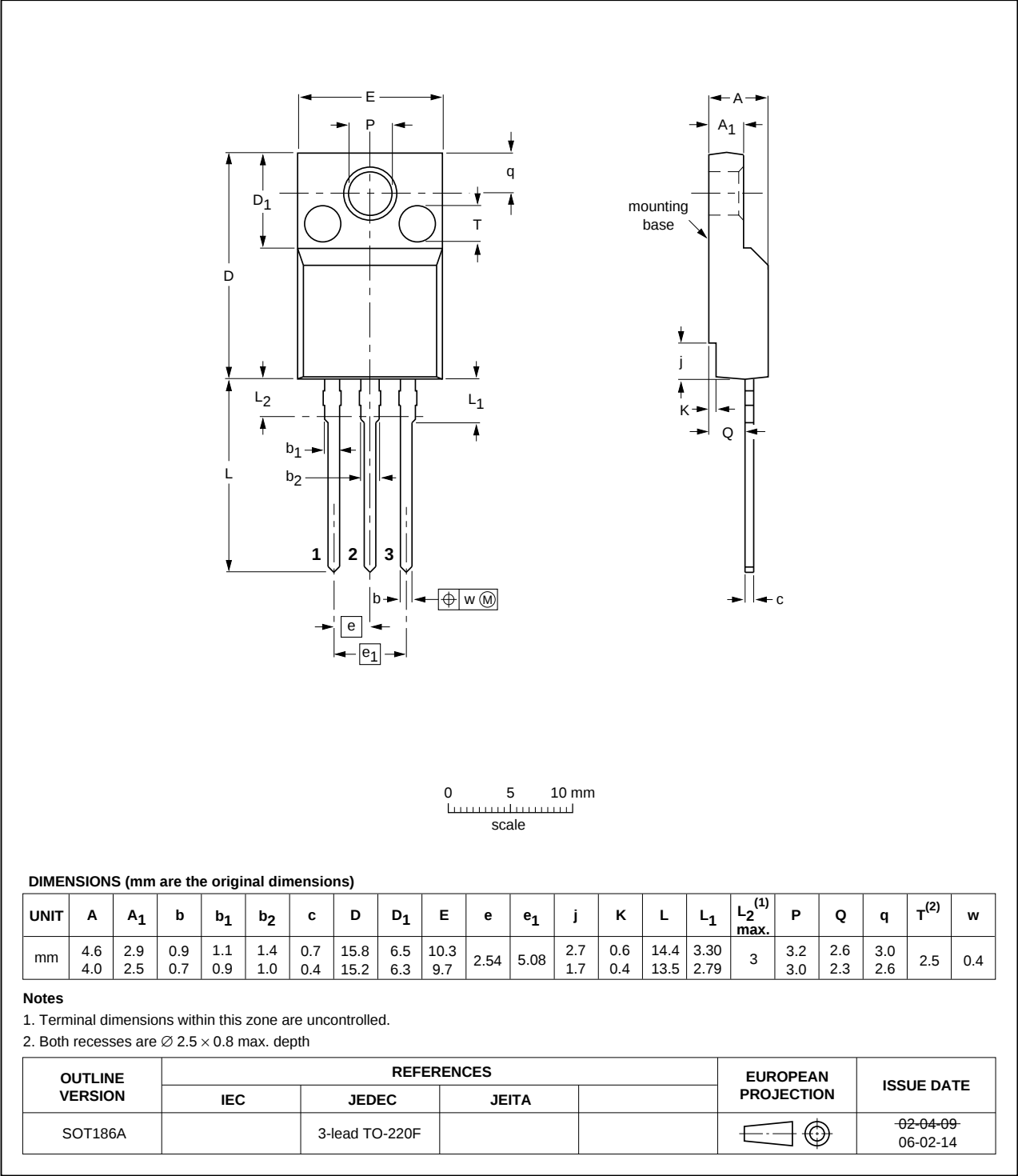


Fig 19. Package outline SOT186A (TO-220F)

## 9. Revision history

**Table 8.** Revision history

| Document ID       | Release date                                                                                                                        | Data sheet status      | Change notice | Supersedes        |
|-------------------|-------------------------------------------------------------------------------------------------------------------------------------|------------------------|---------------|-------------------|
| PSMN9R5-100XS v.3 | 20120306                                                                                                                            | Product data sheet     | -             | PSMN9R5-100XS v.2 |
| Modifications:    | <ul style="list-style-type: none"><li>• Status changed from preliminary to product.</li><li>• Various changes to content.</li></ul> |                        |               |                   |
| PSMN9R5-100XS v.2 | 20111020                                                                                                                            | Preliminary data sheet | -             | PSMN9R5-100XS v.1 |

## 10. Legal information

### 10.1 Data sheet status

| Document status <sup>[1][2]</sup> | Product status <sup>[3]</sup> | Definition                                                                            |
|-----------------------------------|-------------------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet      | Development                   | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet    | Qualification                 | This document contains data from the preliminary specification.                       |
| Product [short] data sheet        | Production                    | This document contains the product specification.                                     |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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## 11. Contact information

For more information, please visit: <http://www.nxp.com>

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